2M (128K x 16) Static RAM

Features

- **High Speed: 55 ns and 70 ns**
- **Wide voltage range: 2.7V–3.6V**
- **Ultra-low active, standby power**
- **Easy memory expansion with $\overline{CE}$ and $\overline{OE}$ features**
- **TTL-compatible inputs and outputs**
- **Automatic power-down when deselected**
- **CMOS for optimum speed/power**
- **Package Available in a standard 44-pin TSOP Type II (forward pinout) package**

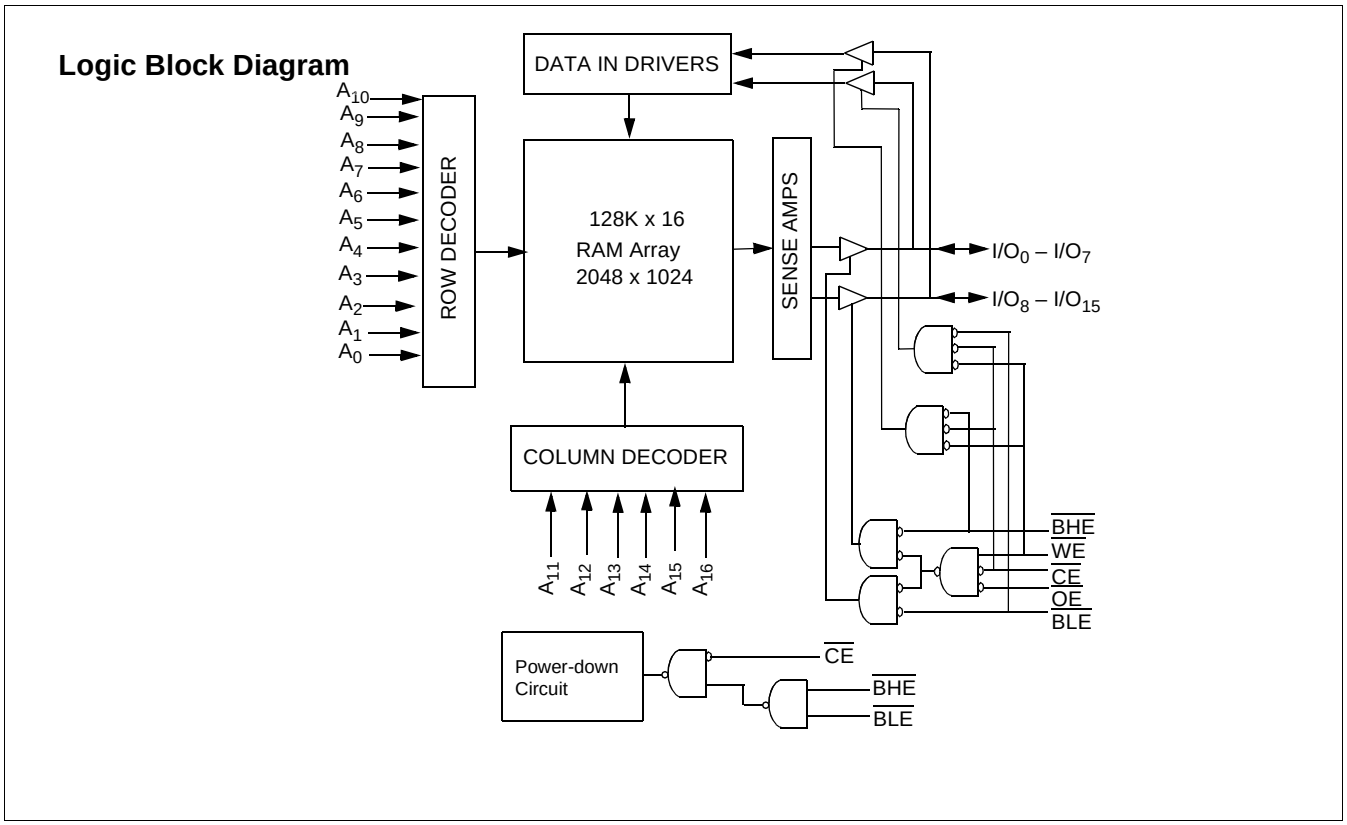
Functional Description[1]

The CY62137V is a high-performance CMOS static RAM organized as 128K words by 16 bits. This device features advanced circuit design to provide ultra-low active current. This is ideal for providing More Battery Life® (MoBL®) in portable applications such as cellular telephones. The device also has an automatic power-down feature that reduces power consumption by 99% when addresses are not toggling. The device can also be put into standby mode when deselected ($\overline{CE}$ HIGH) or when $\overline{CE}$ is LOW and both $\overline{BLE}$ and $\overline{BHE}$ are HIGH. The input/output pins (I/O_0 through I/O_{15}) are placed in a high-impedance state when: deselected ($\overline{CE}$ HIGH), outputs are disabled ($\overline{OE}$ HIGH), $\overline{BHE}$ and $\overline{BLE}$ are disabled ($\overline{BHE}$, $\overline{BLE}$ HIGH), or during a write operation ($\overline{CE}$ LOW, and $\overline{WE}$ LOW).

Writing to the device is accomplished by taking Chip Enable ($\overline{CE}$) and Write Enable ($\overline{WE}$) inputs LOW. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from I/O pins (I/O_0 through I/O_7), is written into the location specified on the address pins (A_0 through A_{16}). If Byte High Enable ($\overline{BHE}$) is LOW, then data from I/O pins (I/O_8 through I/O_{15}) is written into the location specified on the address pins (A_0 through A_{16}).

Reading from the device is accomplished by taking Chip Enable ($\overline{CE}$) and Output Enable ($\overline{OE}$) LOW while forcing the Write Enable ($\overline{WE}$) HIGH. If Byte Low Enable ($\overline{BLE}$) is LOW, then data from the memory location specified by the address pins will appear on I/O_0 to I/O_7. If Byte High Enable ($\overline{BHE}$) is LOW, then data from memory will appear on I/O_8 to I/O_{15}. See the truth table at the back of this data sheet for a complete description of read and write modes.

Logic Block Diagram

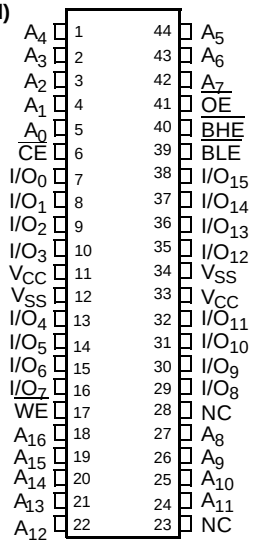


Note:

1. For best practice recommendations, please refer to the Cypress application note "System Design Guidelines" on http://www.cypress.com.

Pin Configurations

TSOP II (Forward)
Top View



Maximum Ratings

(Above which the useful life may be impaired. For user guidelines, not tested.)

Storage Temperature .....–65°C to +150°C

Ambient Temperature with Power Applied.....–55°C to +125°C

Supply Voltage to Ground Potential ..... –0.5V to +4.6V

DC Voltage Applied to Outputs in High-Z State[2] .....–0.5V to V_{CC} + 0.5V

DC Input Voltage[2] ..... –0.5V to V_{CC} + 0.5V

Output Current into Outputs (LOW)..... 20 mA

Static Discharge Voltage..... > 2001V (per MIL-STD-883, Method 3015)

Latch-up Current..... > 200 mA

Operating Range

Range	Ambient Temperature	V_{CC}
Industrial	–40°C to +85°C	2.7V to 3.6V

Product Portfolio

Product	V_{CC} Range (V)			Speed (ns)	Power Dissipation			
					Operating, I_{CC} (mA)		Standby, I_{SB2} (µA)	
	$V_{CC(min.)}$	$V_{CC(typ.)}$[3]	$V_{CC(max.)}$		Typ.[3]	Max.	Typ.[3]	Max.
CY62137VLL	2.7	3.0	3.6	55	7	20	1	15
				70	7	15	1	15
CY62137VSL				55	7	20	1	5
				70	7	15	1	5

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions		CY62137V-55			CY62137V-70			Unit
				Min.	Typ.[3]	Max.	Min.	Typ.[3]	Max.	
V_{OH}	Output HIGH Voltage	I_{OH} = –1.0 mA	V_{CC} = 2.7V	2.4			2.4			V
V_{OL}	Output LOW Voltage	I_{OL} = 2.1 mA	V_{CC} = 2.7V			0.4			0.4	V
V_{IH}	Input HIGH Voltage			2.2		V_{CC} + 0.5V	2.2		V_{CC} + 0.5V	V
V_{IL}	Input LOW Voltage			–0.5		0.8	–0.5		0.8	V
I_{IX}	Input Load Current	GND ≤ V_I ≤ V_{CC}		–1	±1	+1	–1	±1	+1	µA

Notes:
2. V_{IL}(min.) = –2.0V for pulse durations less than 20 ns.
3. Typical values are included for reference only and are not guaranteed or tested. Typical values are measured at V_{CC} = V_{CC} Typ., T_A = 25°C.

Electrical Characteristics Over the Operating Range

Parameter	Description	Test Conditions			CY62137V-55 Min.	CY62137V-55 Typ.[3]	CY62137V-55 Max.	CY62137V-70 Min.	CY62137V-70 Typ.[3]	CY62137V-70 Max.	Unit
I_{OZ}	Output Leakage Current	$GND \le V_O \le V_{CC}$, Output Disabled			–1	±1	+1	–1	±1	+1	µA
I_{CC}	V_{CC} Operating Supply Current	I_{OUT} = 0 mA, f = f_{MAX} = $1/t_{RC}$, CMOS Levels	V_{CC} = 3.6V			7	20		7	15	mA
		I_{OUT} = 0 mA, f = 1 MHz, CMOS Levels				1	2		1	2	mA
I_{SB1}	Automatic CE Power-down Current— CMOS Inputs	$\overline{CE} \ge V_{CC} - 0.3V$, $V_{IN} \ge V_{CC} - 0.3V$ or $V_{IN} \le 0.3V$, f = f_{MAX}	V_{CC} = 3.6V				100			100	µA
I_{SB2}	Automatic CE Power-down Current— CMOS Inputs	$\overline{CE} \ge V_{CC} - 0.3V$ $V_{IN} \ge V_{CC} - 0.3V$ or $V_{IN} \le 0.3V$, f = 0	V_{CC} = 3.6V	LL		1	15		1	15	
				SL		1	5		1	5	

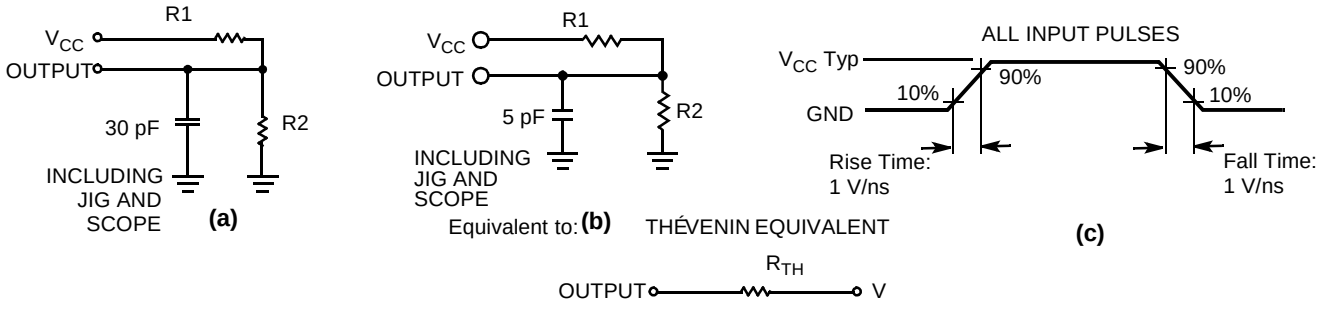
Capacitance[4]

Parameter	Description	Test Conditions	Max.	Unit
C_{IN}	Input Capacitance	T_A = 25°C, f = 1 MHz, $V_{CC} = V_{CC(typ)}$	6	pF
C_{OUT}	Output Capacitance		8	pF

Thermal Resistance

Description	Test Conditions	Symbol	TSOPII	Unit
Thermal Resistance (Junction to Ambient)[4]	Still Air, soldered on a 4.25 x 1.125 inch, 4-layer printed circuit board	Θ_{JA}	60	°C/W
Thermal Resistance (Junction to Case)[4]		Θ_{JC}	22	°C/W

AC Test Loads and Waveforms



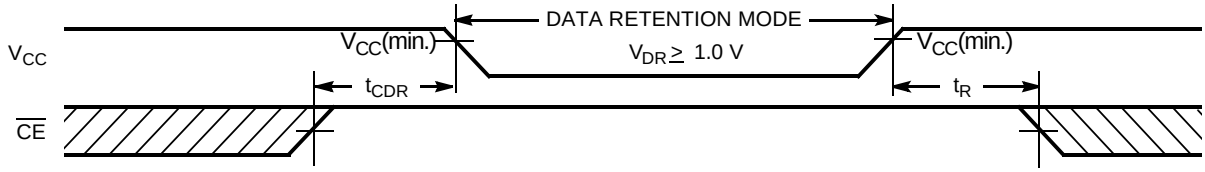
Parameters	3.0V	Unit
R1	1105	Ohms
R2	1550	Ohms
R_{TH}	645	Ohms
V_{TH}	1.75	Volts

Note:
4. Tested initially and after any design or process changes that may affect these parameters.

Data Retention Characteristics (Over the Operating Range)

Parameter	Description	Conditions[5]		Min.	Typ.[3]	Max.	Unit
V_{DR}	V_{CC} for Data Retention			1.0		3.6	V
I_{CCDR}	Data Retention Current	V_{CC} = 1.0V $\overline{CE} \geq V_{CC} - 0.3V$, $V_{IN} \geq V_{CC} - 0.3V$ or $V_{IN} \leq 0.3V$; No input may exceed; V_{CC}+0.3V	LL		0.5	7.5	µA
			SL			5	
t_{CDR}[4]	Chip Deselect to Data Retention Time			0			ns
t_R	Operation Recovery Time			70			ns

Data Retention Waveform



Switching Characteristics Over the Operating Range [5]

Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
Read Cycle						
t_{RC}	Read Cycle Time	55		70		ns
t_{AA}	Address to Data Valid		55		70	ns
t_{OHA}	Data Hold from Address Change	10		10		ns
t_{ACE}	$\overline{CE}$ LOW to Data Valid		55		70	ns
t_{DOE}	$\overline{OE}$ LOW to Data Valid		25		35	ns
t_{LZOE}	$\overline{OE}$ LOW to Low-Z[6]	5		5		ns
t_{HZOE}	$\overline{OE}$ HIGH to High-Z[6, 7]		25		25	ns
t_{LZCE}	$\overline{CE}$ LOW to Low-Z[6]	10		10		ns
t_{HZCE}	$\overline{CE}$ HIGH to High-Z[6, 7]		25		25	ns
t_{PU}	$\overline{CE}$ LOW to Power-up	0		0		ns
t_{PD}	$\overline{CE}$ HIGH to Power-down		55		70	ns
t_{DBE}	$\overline{BHE}$ / $\overline{BLE}$ LOW to Data Valid		55		70	ns
t_{LZBE} (8)	$\overline{BHE}$ / $\overline{BLE}$ LOW to Low-Z	5		5		ns
t_{HZBE}	$\overline{BHE}$ / $\overline{BLE}$ HIGH to High-Z		25		25	ns
Write Cycle[9, 10]						
t_{WC}	Write Cycle Time	55		70		ns
t_{SCE}	$\overline{CE}$ LOW to Write End	45		60		ns
t_{AW}	Address Set-up to Write End	45		60		ns
t_{HA}	Address Hold from Write End	0		0		ns
t_{SA}	Address Set-up to Write Start	0		0		ns
t_{PWE}	$\overline{WE}$ Pulse Width	40		50		ns

Notes:

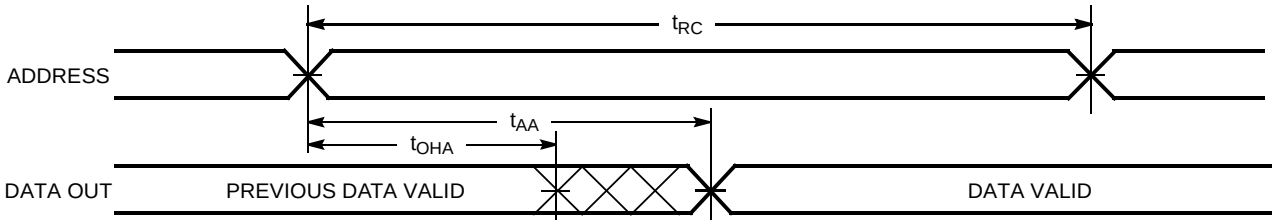
5. Test conditions assume signal transition time of 5 ns or less, timing reference levels of 1.5V, input levels of 0 to V_{CC} typ., and output loading of the specified I_{OL}/I_{OH} and 30 pF load capacitance.
6. At any given temperature and voltage condition, t_{HZCE} is less than t_{LZCE}, t_{HZOE} is less than t_{LZOE}, and t_{HZWE} is less than t_{LZWE} for any given device.
7. t_{HZOE}, t_{HZCE}, and t_{HZWE} are specified with C_L = 5 pF as in (b) of AC Test Loads. Transition is measured ±500 mV from steady-state voltage.
8. If both byte enables are toggled together this value is 10 ns.
9. The internal write time of the memory is defined by the overlap of $\overline{CE}$ LOW and $\overline{WE}$ LOW. Both signals must be LOW to initiate a write and either signal can terminate a write by going HIGH. The data input set-up and hold timing should be referenced to the rising edge of the signal that terminates the write.
10. The minimum write cycle time for write cycle #3 ($\overline{WE}$ controlled, $\overline{OE}$ LOW) is the sum of t_{HZWE} and t_{SD}.

Switching Characteristics Over the Operating Range (continued) [5]

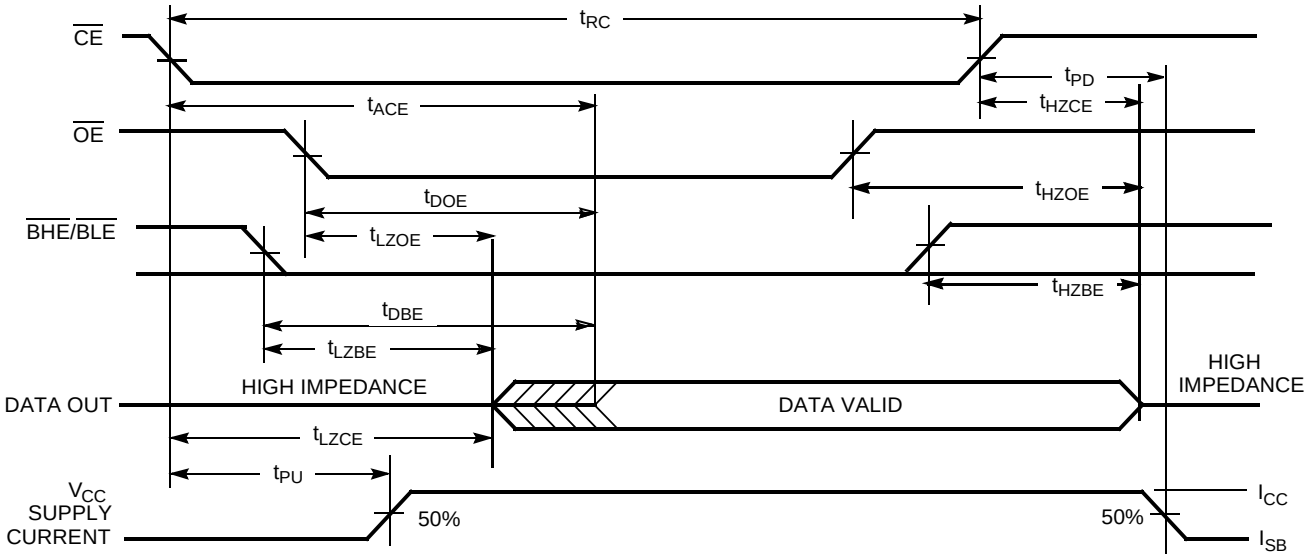
Parameter	Description	55 ns		70 ns		Unit
		Min.	Max.	Min.	Max.	
t_{SD}	Data Set-up to Write End	25		30		ns
t_{HD}	Data Hold from Write End	0		0		ns
t_{HZWE}	$\overline{WE}$ LOW to High-Z[6, 7]		20		25	ns
t_{LZWE}	$\overline{WE}$ HIGH to Low-Z[6]	5		10		ns
t_{BW}	$\overline{BHE}$ / $\overline{BLE}$ LOW to End of Write	50		60		ns

Switching Waveforms

Read Cycle No. 1 [11, 12]



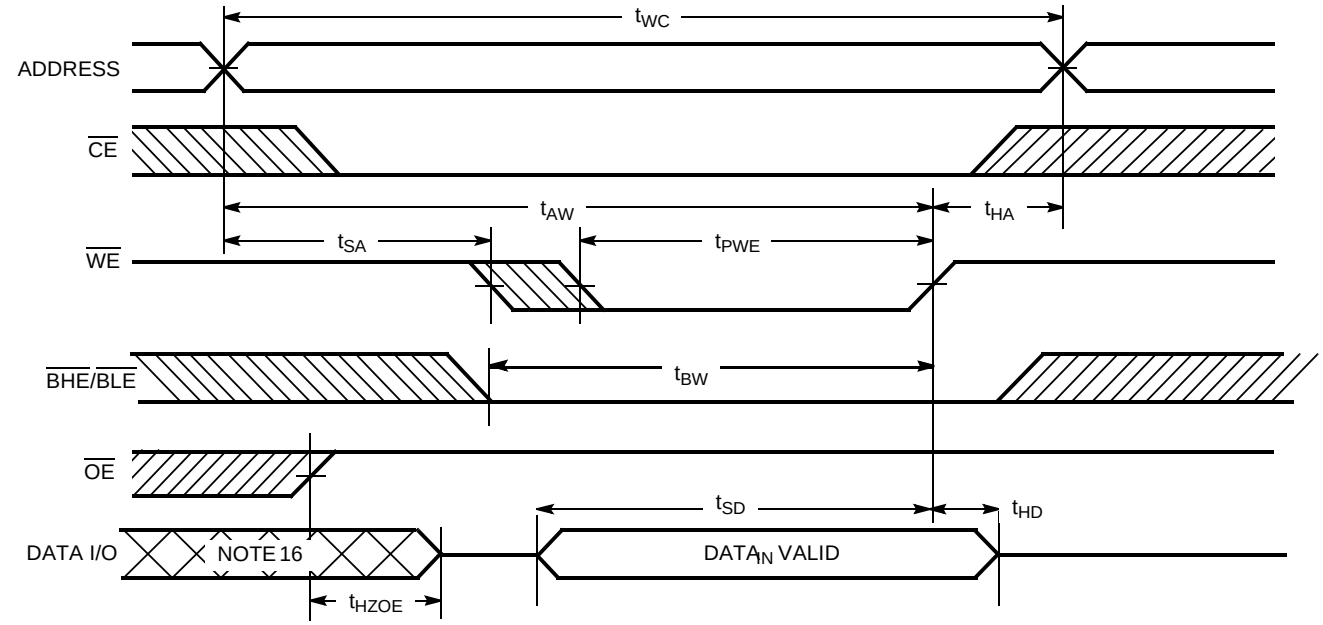
Read Cycle No. 2 [12, 13]



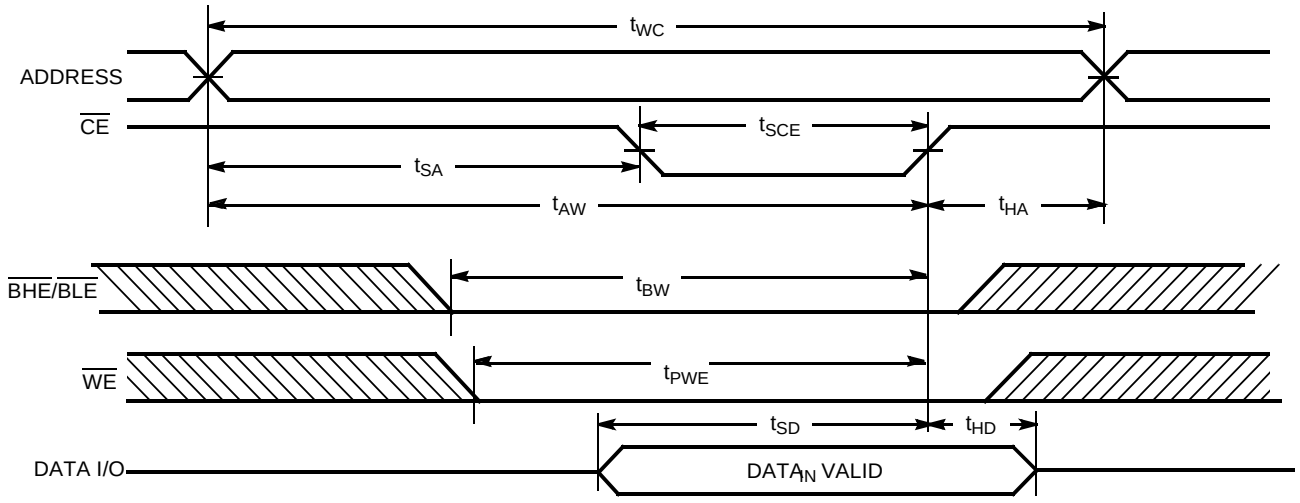
Notes:
11. Device is continuously selected. $\overline{OE}$, $\overline{CE}$ = V_{IL}.
12. $\overline{WE}$ is HIGH for read cycle.
13. Address valid prior to or coincident with $\overline{CE}$ transition LOW.

Switching Waveforms (continued)

Write Cycle No. 1 ($\overline{WE}$ Controlled)[9, 14, 15]



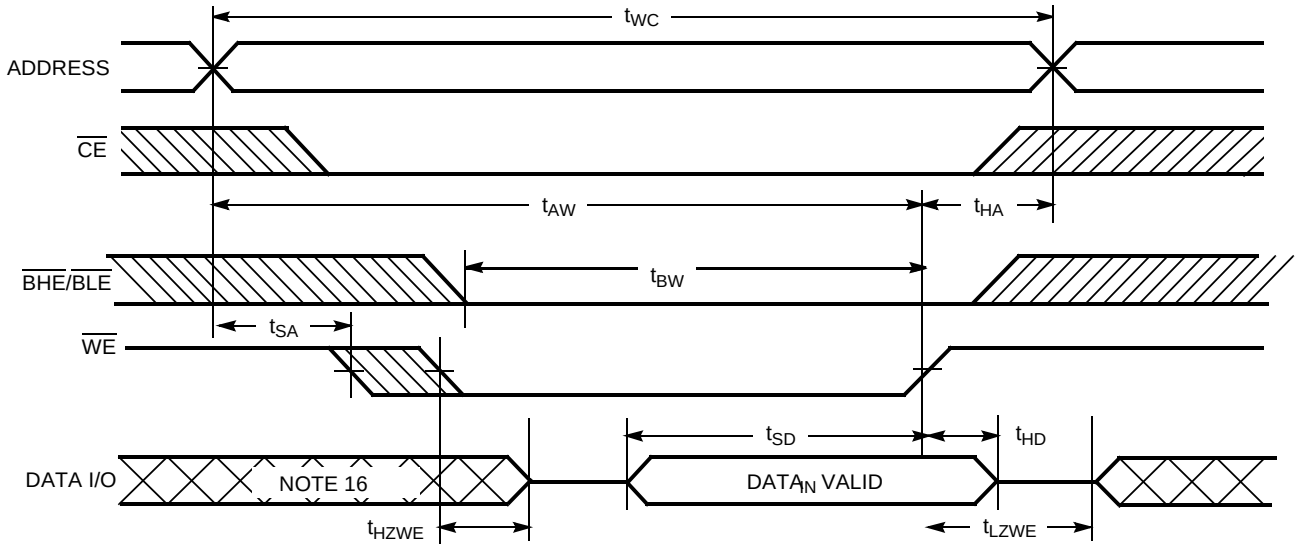
Write Cycle No. 2 ($\overline{CE}$ Controlled)[9, 14, 15]



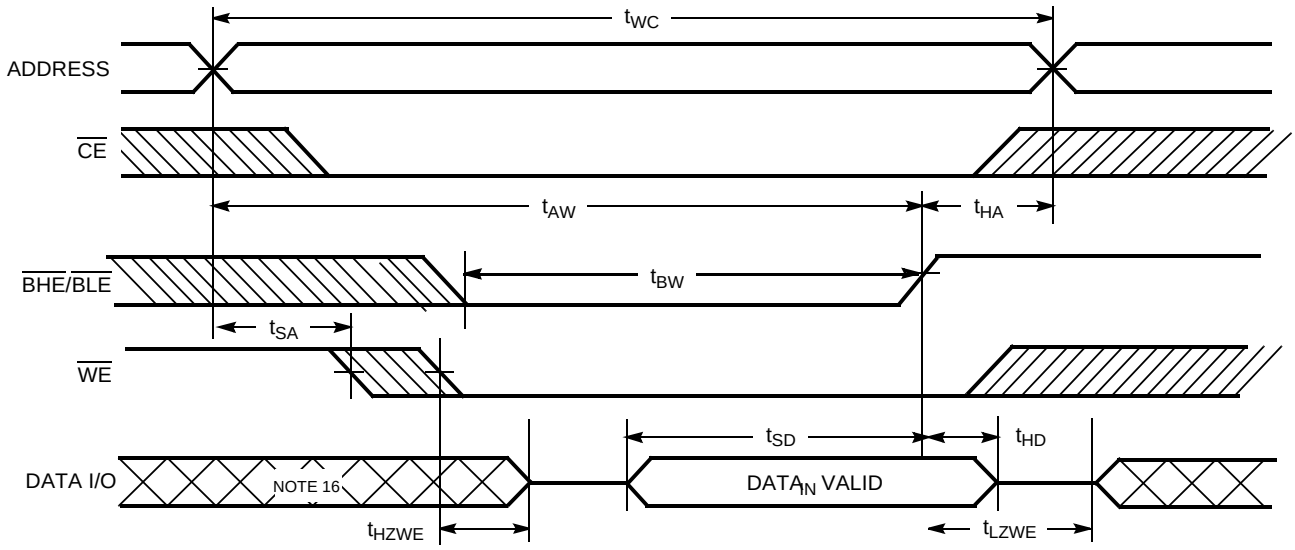
Notes:
14. Data I/O is high-impedance if $\overline{OE} = V_{IH}$.
15. If $\overline{CE}$ goes HIGH simultaneously with $\overline{WE}$ HIGH, the output remains in a high-impedance state.
16. During this period, the I/Os are in output state and input signals should not be applied.

Switching Waveforms (continued)

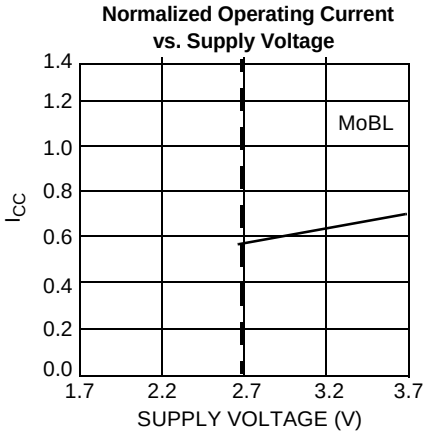
Write Cycle No. 3 (WE Controlled, OE LOW)[10, 15]

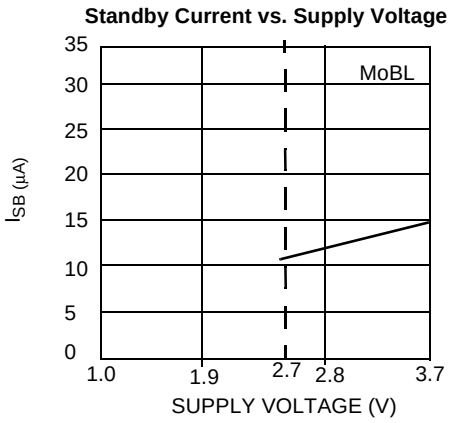


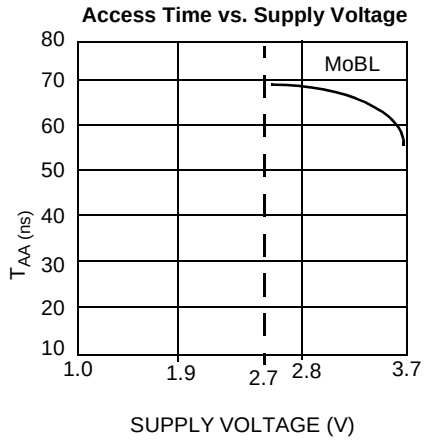
Write Cycle No. 4 (BHE/BLE Controlled, OE LOW)[16]



Typical DC and AC Characteristics







Truth Table

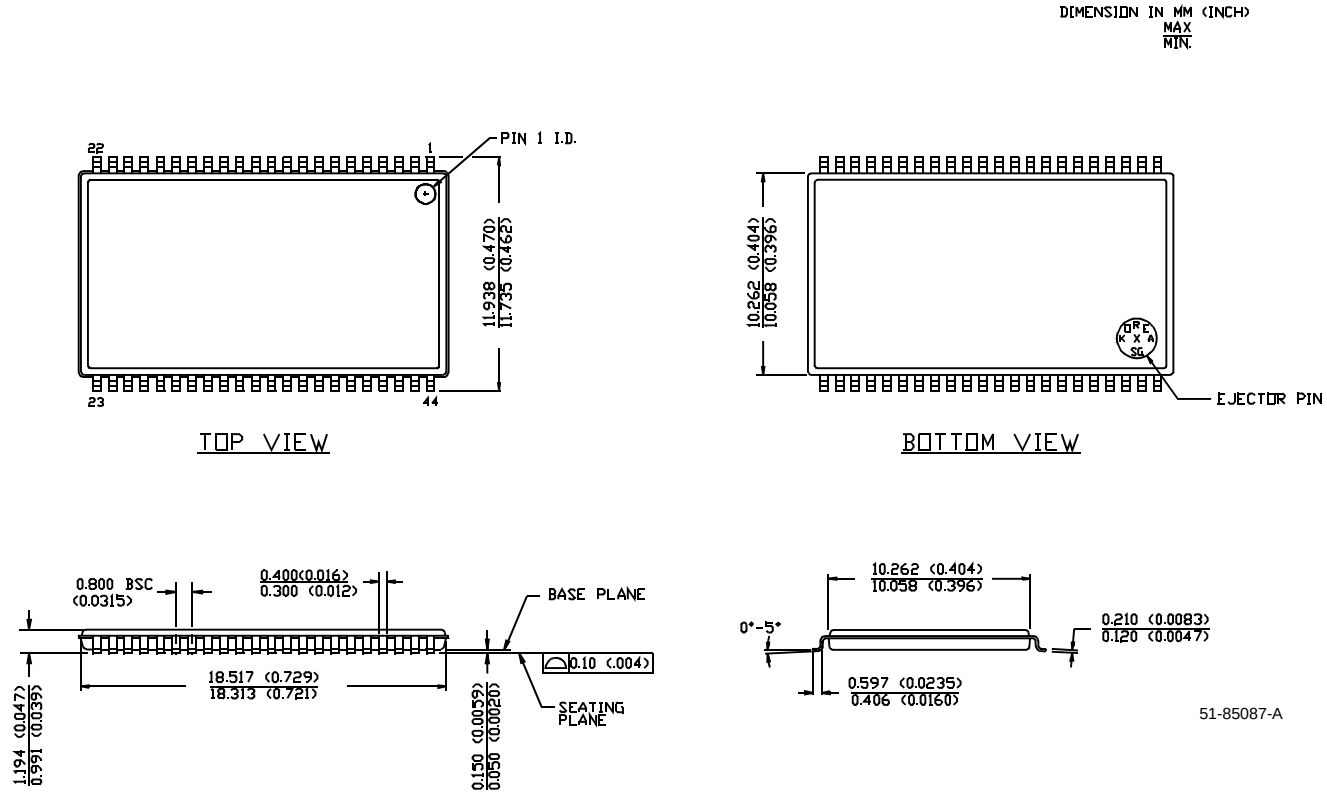
$\overline{CE}$	$\overline{WE}$	$\overline{OE}$	$\overline{BHE}$	$\overline{BLE}$	Inputs/Outputs	Mode	Power
H	X	X	X	X	High-Z	Deselect/Power-down	Standby (I_{SB})
L	X	X	H	H	High-Z	Deselect/Power-down	Standby (I_{SB})
L	H	L	L	L	Data Out (I/O_O–I/O_{15})	Read	Active (I_{CC})
L	H	L	H	L	Data Out (I/O_O–I/O_7); I/O_8–I/O_{15} in High-Z	Read	Active (I_{CC})
L	H	L	L	H	Data Out (I/O_8–I/O_{15}); I/O_0–I/O_7 in High-Z	Read	Active (I_{CC})
L	H	H	L	L	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	H	L	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	H	H	L	H	High-Z	Deselect/Output Disabled	Active (I_{CC})
L	L	X	L	L	Data In (I/O_O–I/O_{15})	Write	Active (I_{CC})
L	L	X	H	L	Data In (I/O_O–I/O_7); I/O_8–I/O_{15} in High-Z	Write	Active (I_{CC})
L	L	X	L	H	Data In (I/O_8–I/O_{15}); I/O_0 –I/O_7 in High-Z	Write	Active (I_{CC})

Ordering Information

Speed (ns)	Ordering Code	Package Name	Package Type	Operating Range
55	CY62137VLL-55ZI	Z44	44-pin TSOP II	Industrial
	CY62137VSL-55ZI			
70	CY62137VLL-70ZI			
	CY62137VSL-70ZI			

Package Diagrams

44-pin TSOP II Z44



MoBL is a registered trademark, and More Battery Life is a trademark, of Cypress Semiconductor. All product and company names mentioned in this document are the trademarks of their respective holders.

Document Title: CY62137V MoBL® 2M (128K x 16) Static RAM Document Number: 38-05051				
REV.	**ECN NO.**	**Issue Date**	**Orig. of Change**	**Description of Change**
**	109960	10/03/01	SZV	Changed from Spec number: 38-00738 to 38-05051
A	116788	09/04/02	GBI	Added footnote number one. Added SL power bin. Deleted fBGA package; replacement fBGA package is available in CY62137CV30.